

# **COMPOUND TRANSISTOR** AA1L3N

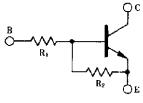
# on-chip resistor NPN silicon epitaxial transistor For mid-speed switching

### **FEATURES**

· On-chip bias resistor  $(R_1 = 4.7 \text{ k}\Omega, R_2 = 10 \text{ k}\Omega)$ 

Complementary transistor with AN1L3N

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

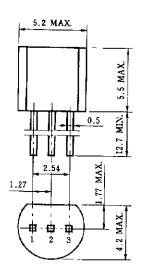


#### Parameter Symbol Unit Ratings Collector to base voltage v Vсво 60 Collector to emitter voltage 50 v VCEO Emitter to base voltage Vево 5 ٧ Collector current (DC) 100 C(DC) mΑ Collector current (Pulse) IC(pulse) \* 200 mΑ Ρт 250 mW Total power dissipation °C Junction temperature Tj 150 °C -55 to +150 Storage temperature Tstg

 $PW \le 10 \text{ ms}$ , duty cycle  $\le 50 \%$ 

# ELECTRICAL CHARACTERISTICS (Ta = 25°C)

# PACKAGE DRAWING (UNIT: mm)



Electrode Connection

1. Emitter EIAJ : SC-43B

2. Collector JEDEC: TO-92 3. Base

IEC : PA33

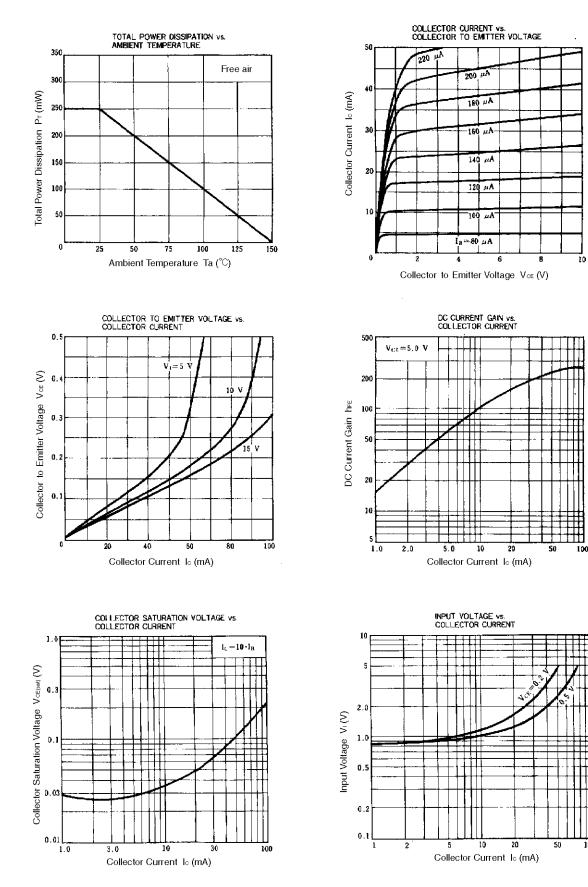
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	Vcb = 50 V, IE = 0			100	nA
DC current gain	hfe1 **	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 5.0 \text{ mA}$	35	60	100	-
DC current gain	hfe2 **	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 50 \text{ mA}$	80	230		-
Collector saturation voltage	VCE(sat) **	lc = 5.0 mA, I <sub>B</sub> = 0.25 mA		0.05	0.2	V
Low level input voltage	VIL **	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 100 \ \mu\text{A}$		0.9	0.6	V
High level input voltage	ViH **	$V_{CE} = 0.2 \text{ V}, \text{ Ic} = 5.0 \text{ mA}$	3.0	1.5		V
Input resistance	R1		3.29	4.7	6.11	kΩ
E-to-B resistance	R2		7	10	13	kΩ
Turn-on time	ton	$V_{CC} = 5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega$			0.2	μs
Storage time	tstg	$V_i = 5 V, PW = 2 \mu s$			5.0	μs
Turn-off time	toff	duty cycle≤2 %			6.0	μs

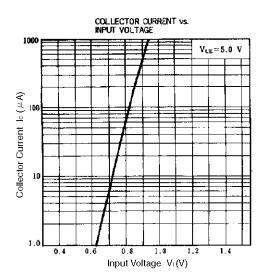
\*\* Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2 %

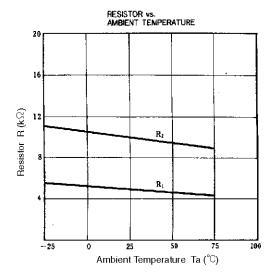
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## TYPICAL CHARACTERISTICS (Ta = 25°C)







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